



LASER DIODES FOR NEXT GENERATION LIGHT SOURCES

Providing the brightest, most efficient
laser light sources to the world

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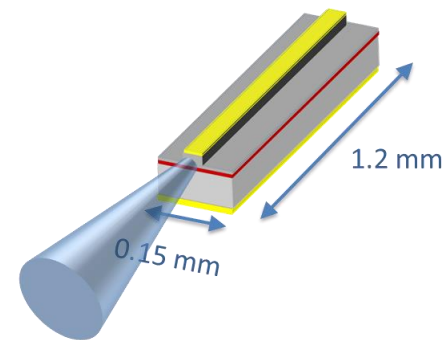
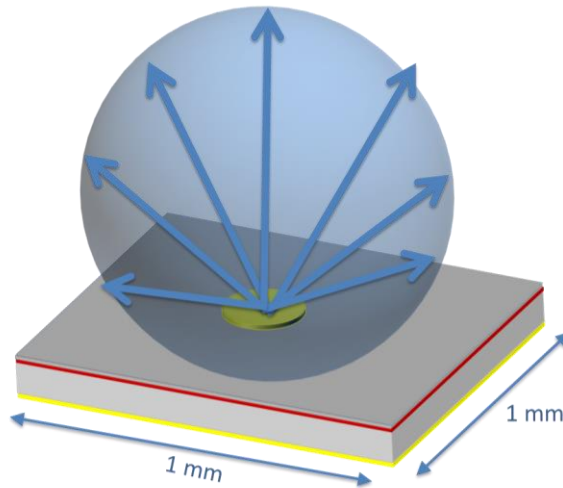
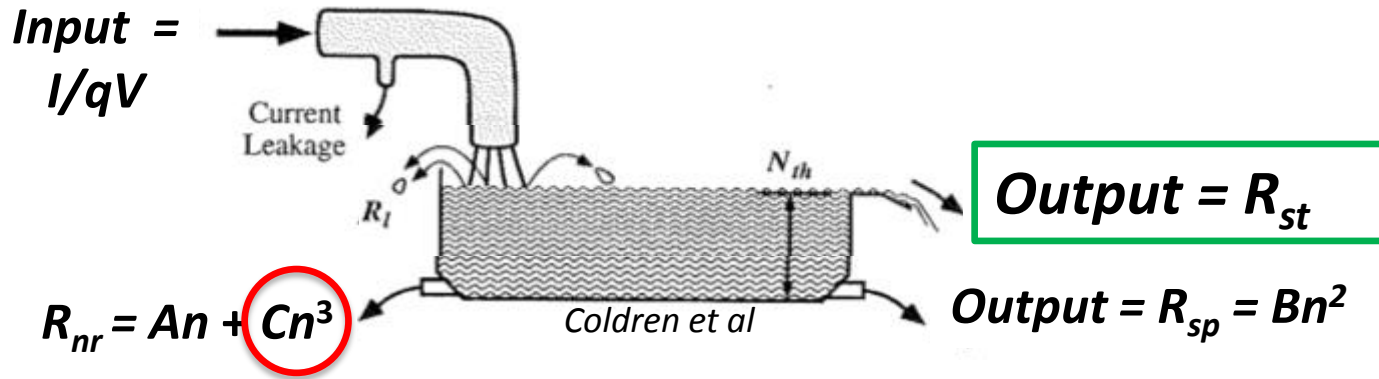
DOE SSL R&D Workshop

Raleigh, NC February 3, 2016

- LDs are solution to droop and offer 10-20X more power per chip area and 10,000X the spatial brightness of LEDs
 - LD + phosphor source can provide superior “delivered” lm/W
- LDs must overcome challenges such as wall plug efficiency to achieve maximum adoption in lighting
 - Evolution of GaAs LDs paved a proven pathway for GaN LDs
- GaN LDs have a bright future

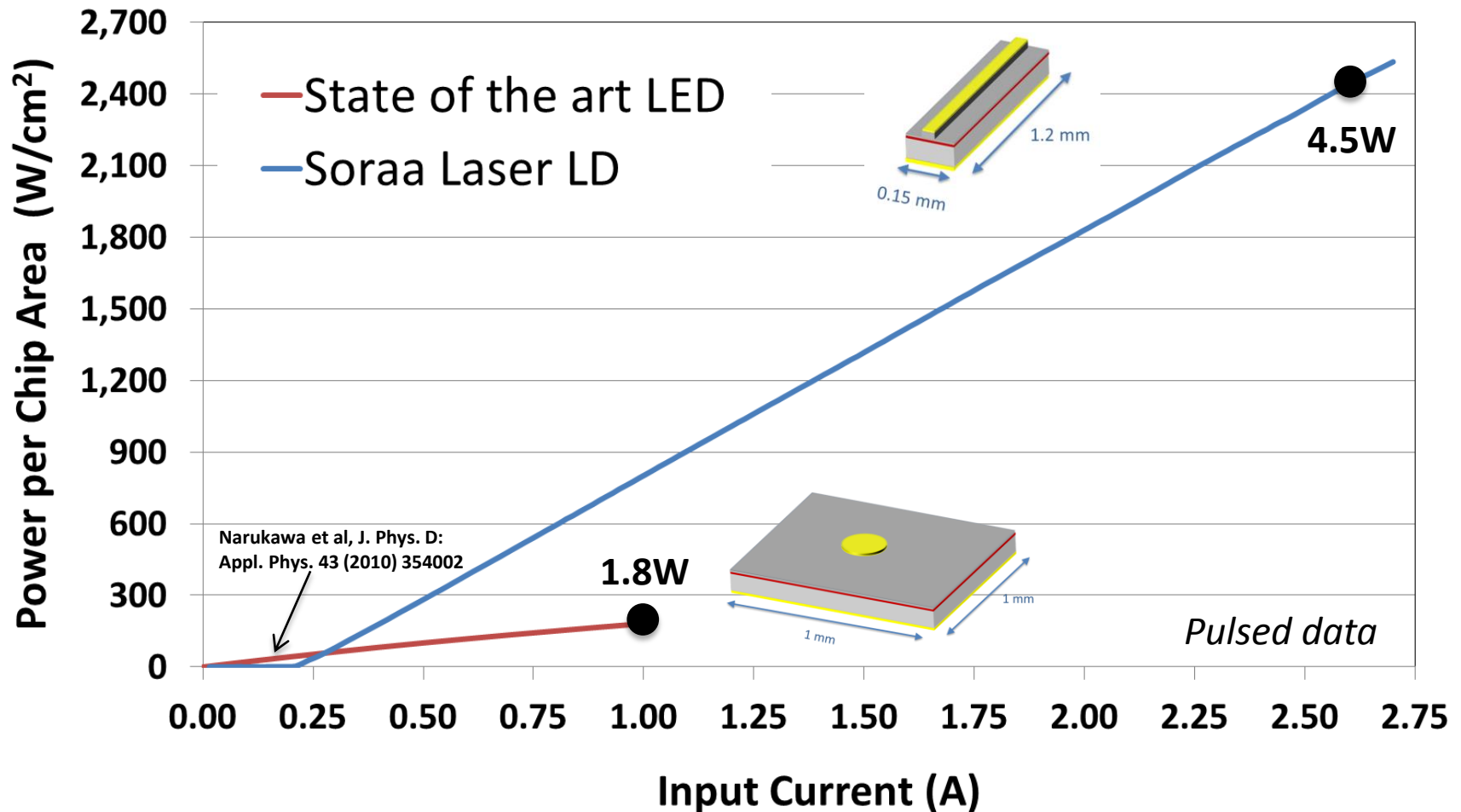


Laser Diode



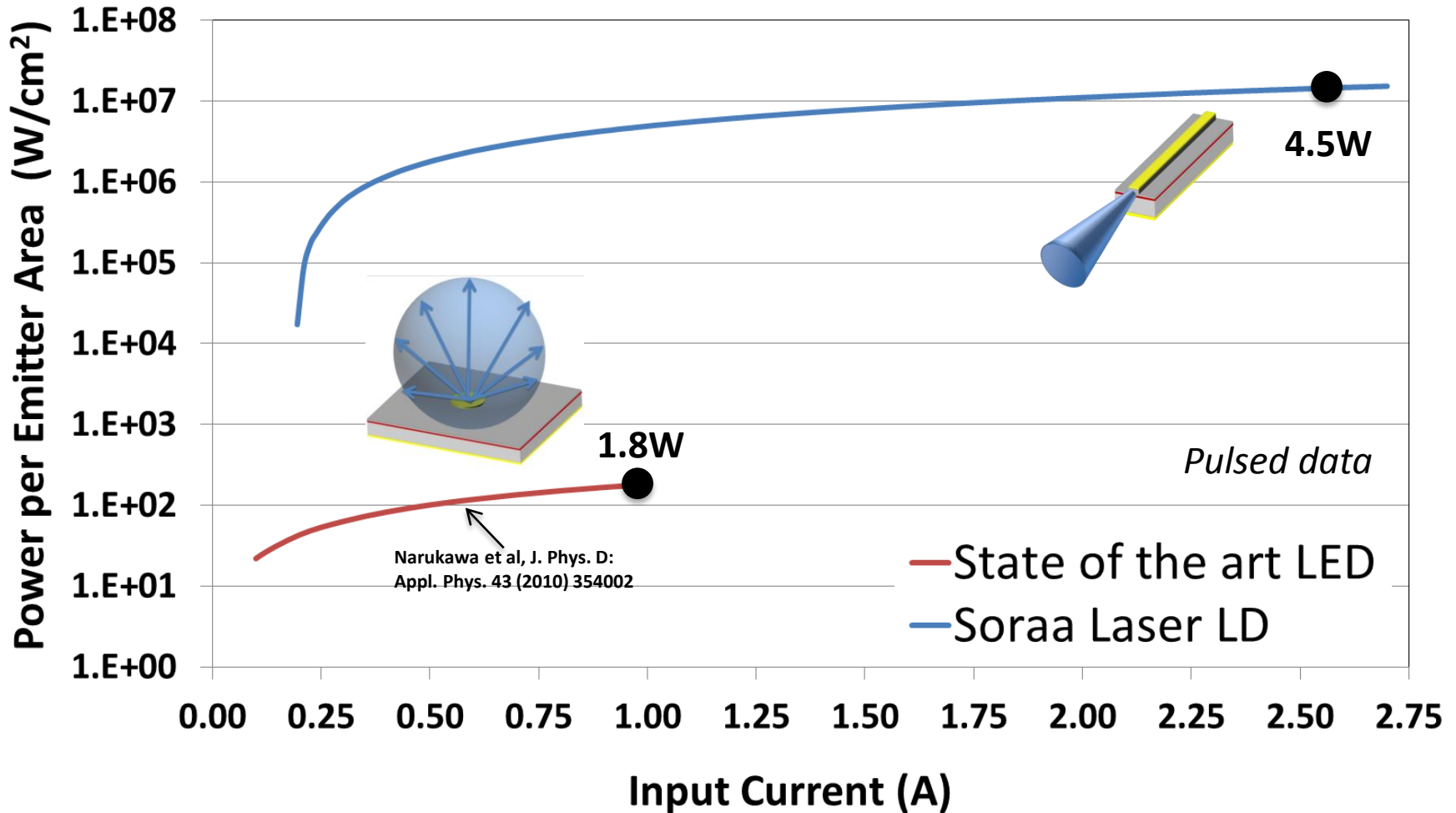
LED vs LD: POWER PER CHIP AREA

Current LDs produce 10-20X more light per chip area



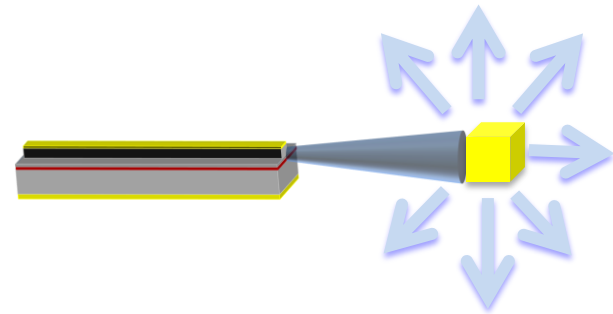
LED vs LD: OUTPUT POWER DENSITY

LD aperture 10,000X brighter than LED emitter



- Low etendue + high brightness make LDs ideal excitation source

| |
|--|
| LD + Phosphor |
| 3W in $<100\mu\text{m}$ \varnothing spot on phosphor |
| $>380 \text{ W/mm}^2$ |



LDs $>300\text{X}$ brighter than LED: Superior for directional applications
Even with $\frac{1}{2}$ the WPE, LDs can provide higher delivered lm/W

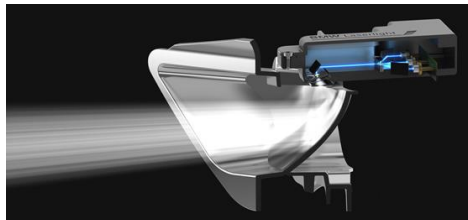
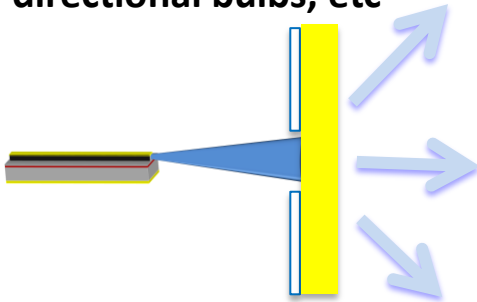


LD + PHOSPHOR CONFIGURATIONS

- Phosphor technology for high power density LD excitation exists today
 - Ceramic and single-crystal YAG:CE demonstrate low thermal quenching, high IQE, and robust lifetimes at >200C
- Infinite number of LD + phosphor configurations; Opportunity

Transmission

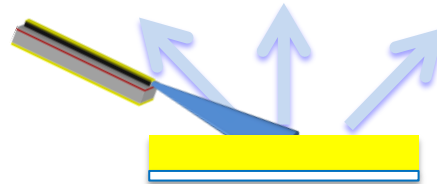
e.g. spotlights, headlights, directional bulbs, etc



BMW I8; motorauthority.com

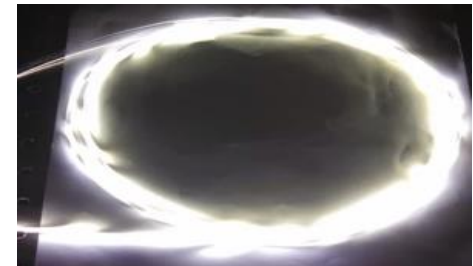
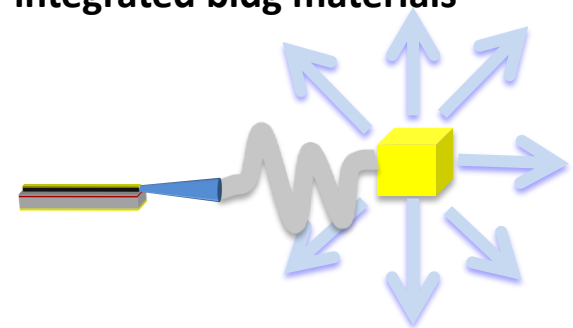
Reflection

e.g. spotlights, headlights, directional bulbs, etc



Remote: T or R

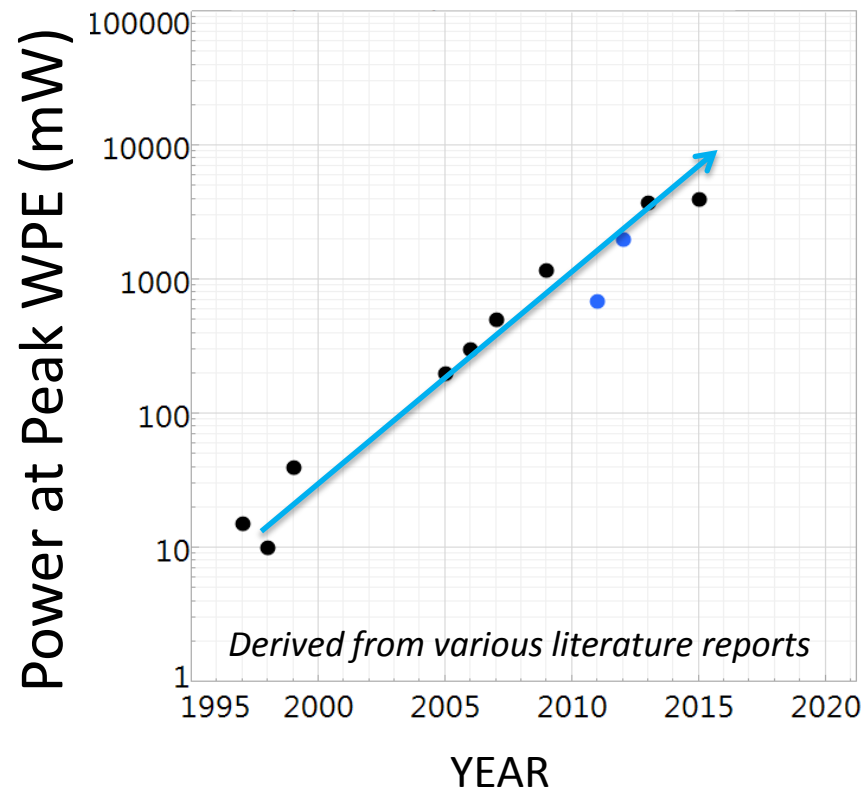
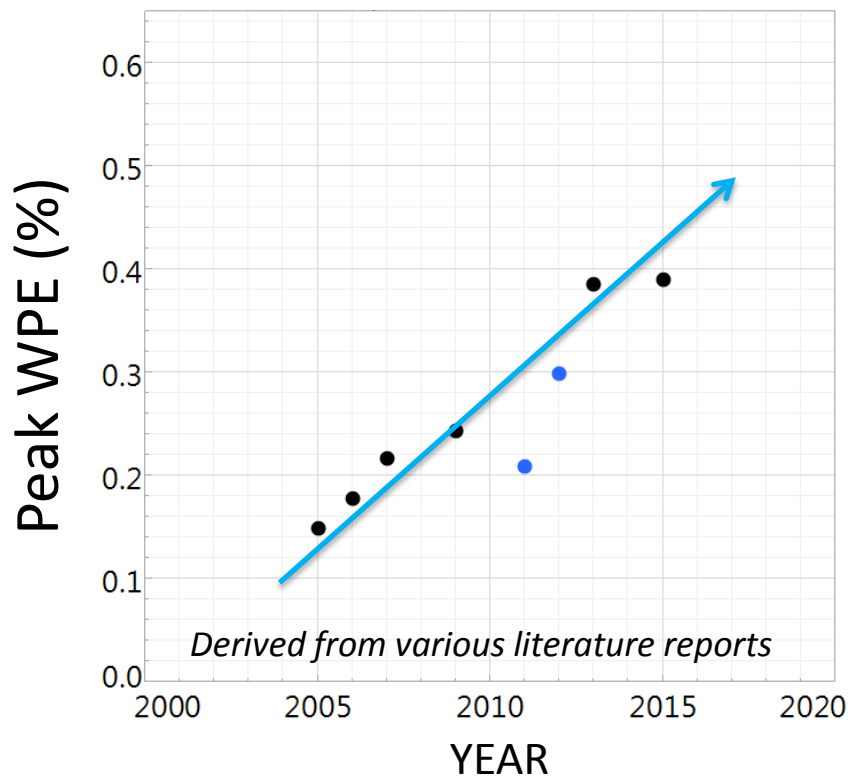
e.g. street, bridge, tunnel light; integrated bldg materials



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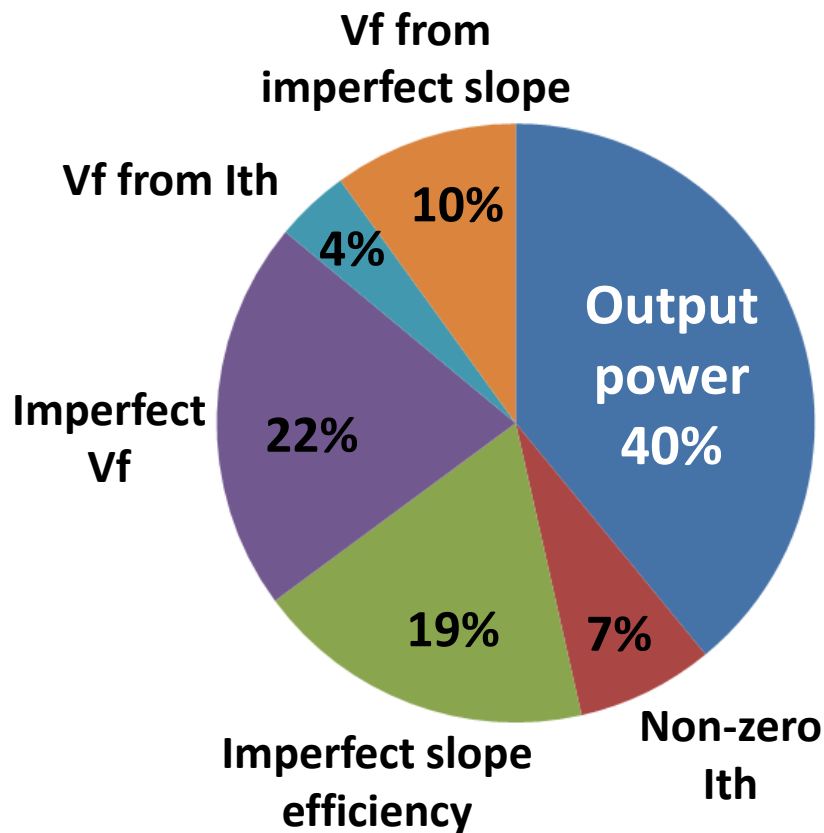


LD WPE @ ~40% w/ RAPID PROGRESS



- Blue LD WPE increased from 15% in 2005 to ~40% in 2015
- P @ max WPE increased from 10mW in 1997 to 4W in 2015

Example 4W/40% WPE Blue LD;



$$WPE = EQE \left(\frac{h\nu}{qV} \right)$$

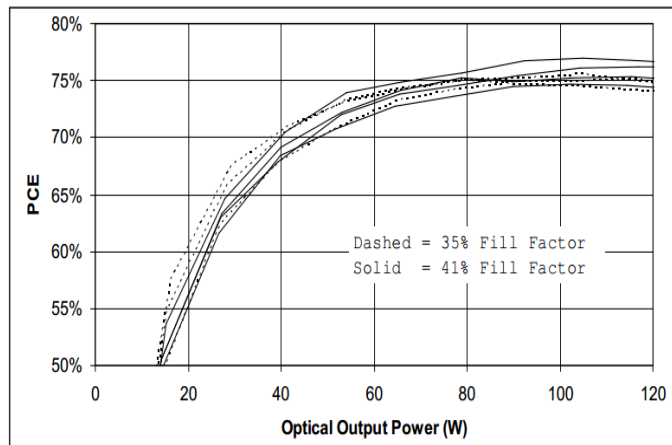
$$n_{inj} \frac{a_m}{a_m + a_i} \frac{(I - I_{th})}{I}$$

| LD | GaN | GaAs |
|--------------------------------|-----------|-----------|
| WPE (%) | 35 - 40 | 75 - 80 |
| η_{inj} (%) | >80 | >95 |
| α_i (cm ⁻¹) | 1.0 - 3.0 | 0.3 - 0.5 |
| $h\nu/qV$ (V) | >1.5 | 0.15 |

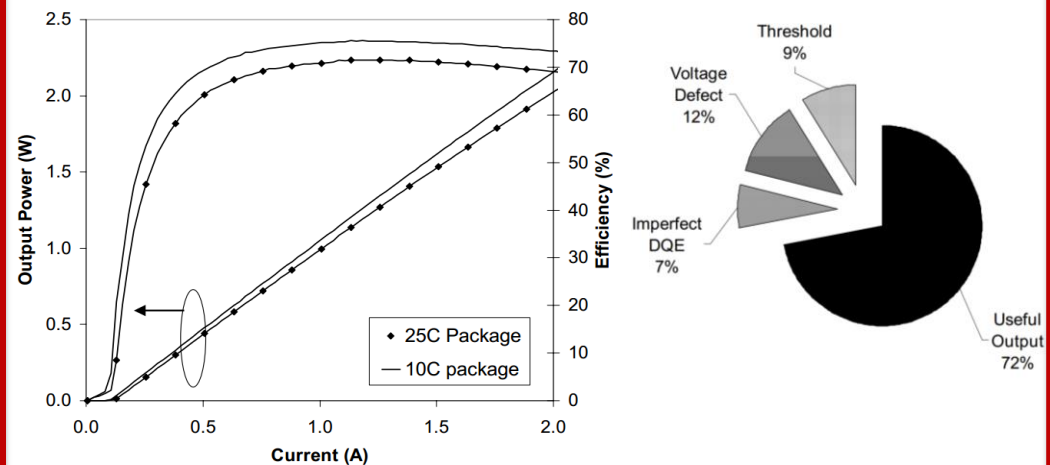
SHEDS: A MODEL TO DRIVE GaN LD WPE

- In 2003 DoD launched SHEDS (super-high-efficiency diode sources)
 - Featured 8 partners; JDSU, nLight, Alphalight, several universities etc
- Program goal to drive GaAs 9xx nm LDs from 45-50% to 80% WPE
 - Motivated by interest to improve the efficiency of diode-pumped solid-state lasers
- SHEDS was huge success driving WPE 75-85% by program end;
 - In <1 year achieved 65% WPE, by program end in 2006, ~75% WPE at RT and 85% at -50C

JDSU; Peters et al, 2005



nLIGHT; Crump et al, 2005



Cost

Volume driven; LD fab yield, substrate costs, etc
GaAs LD pathway mapped to <\$0.03/W in studies

Lifetime/Reliability

Low defect densities and optimized process
Wide stripe, specialized facet coating technology

Thermal Management

Current 4W LD has >400X waste power density of 1W LED
P-side down bond, thermal materials, remote light

Eye Safety Concerns

Laser + phosphor; Design for safety will be key element
Laser based projectors already in wide-spread use



LDs offer inherent benefits over LEDs; Next Gen light sources

- LDs are Droop-Free at >100x current density
- LDs are 10,000x brighter and can yield 10-20x more power from epi area
- LD sources already provide superior “delivered lm/W” in directional apps

LD adoption will grow with tech maturity and Next Gen lighting

- GaAs LDs paved a proven pathway towards performance and cost for GaN LDs
- SHEDs as example of a program to drive GaN LDs to GaN LED efficiencies
- Benefits of LDs will become further attractive in Next Gen lighting

Thank you for your attention